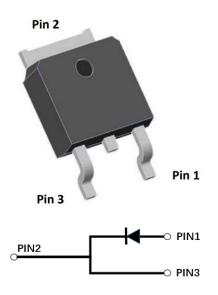






Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (135°C)}	3.5A
Qc	5.2nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106502DQG3
Reverse voltage (repetitive peak) @ T _i =25°C	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	650
Continuous forward current @ T _c =25°C			7.2
Continuous forward current @ T _c =135°C	I _F	Α	3.5
Continuous forward current @ T _c =160°C			2
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	20
Power Dissipation@ T _c =25°C	P _{TOT}	w	42
Power Dissipation@ T _c =110°C	ГТОТ	VV	18
i²t Value@ Tc=25°C ,tp=10ms	∫i²dt	A ² S	2
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

YJD106502DQG3

■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =2A, T _j =25°C	1.5	1.6
r orward voltage drop	V _F V	I _F =2A, T _j =175°C	2.2	-	
Reverse leakage current			V _R =650V, T _j =25°C	0.1	10
Reverse leakage current	I _R μA	μΑ	V _R =650V, T _j =175°C	1	-
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C, $QC=\int_0^{VR}C(V)dV$	5.2	-
			V _R =0V, f=1MHZ	84	-
Total capacitance	С	pF	V _R =200V, f=1MHZ	9.8	-
	V _R =	V _R =400V, f=1MHZ	9.4	-	
Capacitance Stored Energy	Ec	μJ	V _R =400V	0.6	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{eJ-C}	°C W	3.62

■Typical Characteristics

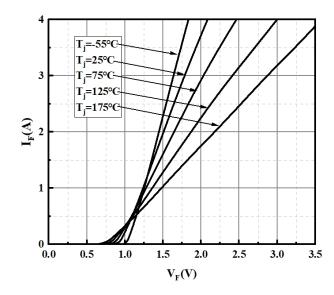


Figure 1. Forward Characteristics

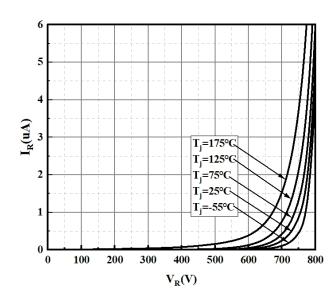
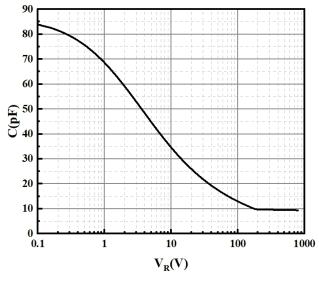


Figure2. Reverse Characteristic





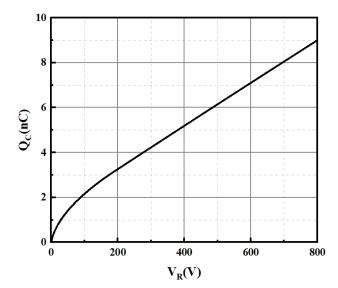
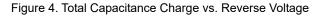
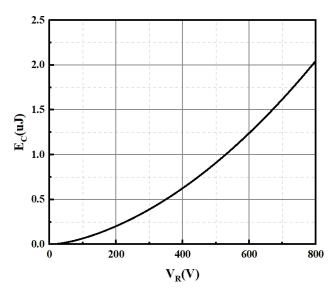


Figure 3. Capacitance vs. Reverse Voltage





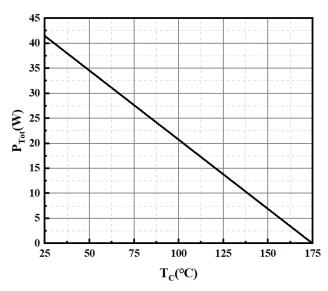
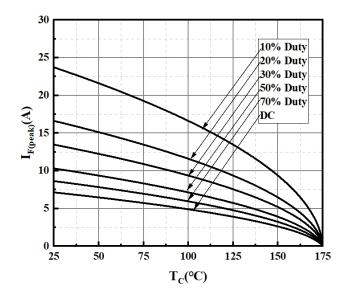


Figure 5. Capacitance Stored Energy

Figure 6. Power Derating



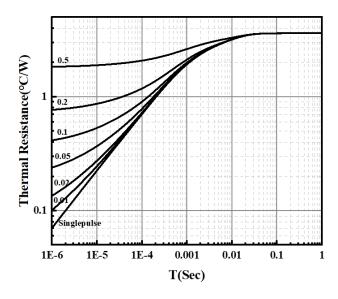


Figure 7. Current Derating

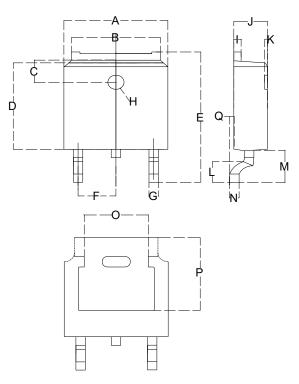
Figure 8. Transient Thermal Impedance





■Outline Dimensions

TO-252



Dimensions in millimeters

TO-252		
Dim	Min	Max
Α	6.500	6.700
В	5.100	5.460
С	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
Н	Ф1.050	Ф1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
М	2.730	3.080
N	0.430	0.580
0	4.20	4.95
Р	5.15	5.45
Q	0	0.2



YJD106502DQG3

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